SEP 1 5 2005

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Attorney Docket'No.:021653-002300US
Title: Monitoring Low Temperature Rapid Thermal Anneal Process Using Implanted Wafers
Applicants: Jingang Wu, et al.
Replacement Sheet 1 of 5

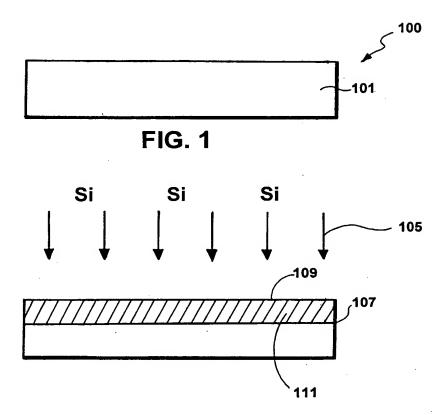


FIG. 2

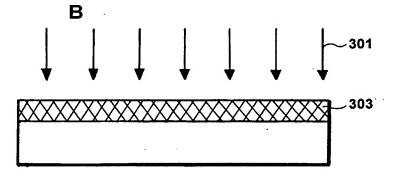
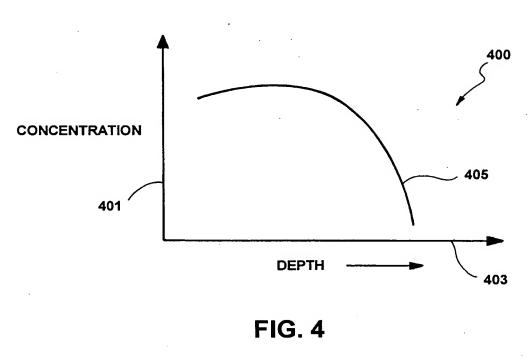


FIG. 3



Si — Si Si B Si — Si Si 453

FIG. 4A

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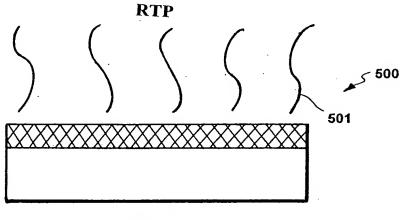


FIG. 5

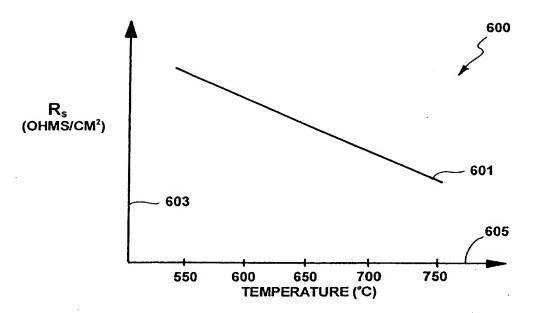


FIG. 6



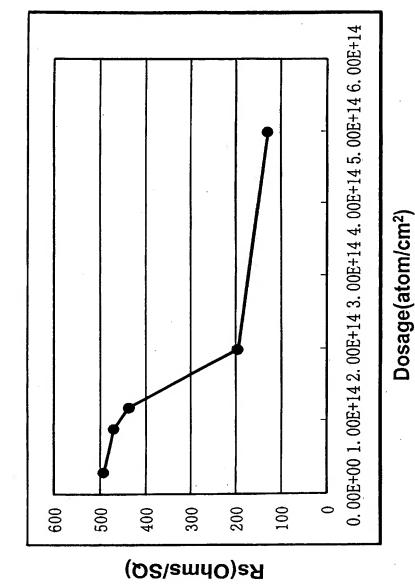


Figure 7: Changes of Rs as a function of implant dosage of silicon, Boron dosage unchanged (3.5E15).



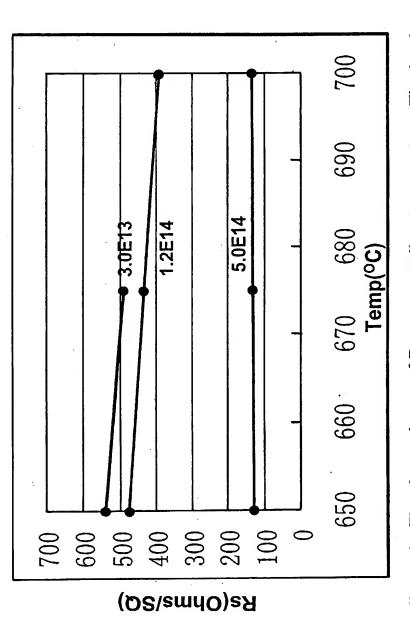


Figure 8: The dependence of Rs on annealing temperature. The implant dose of silicon varied from 3.0E13 to 5.0E14, Boron dosage unchanged (3.5E15).

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